



Product brief

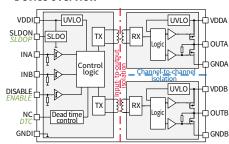
Dual-channel isolated EiceDRIVER™ family

Fast, robust, dual-channel, functional and reinforced isolated Si and SiC MOSFET gate driver ICs with accurate and stable timing

Overview

The dual-channel isolated EiceDRIVER™ product family is designed for the use in high-performance power conversion applications. Very strong 4 A/8 A source/sink dual-channel gate drivers increase efficiency in CoolMOS™, CoolSiC™ and OptiMOS™ MOSFET half-bridges. The low propagation delay of 37 ns, combined with highly accurate and stable timing overtemperature and production, enables further efficiency gains within and across galvanically isolated power stages or in multi-phase/multi-level topologies. The availability of functional and reinforced isolated drivers in different packages makes these a perfect fit for both primary side and (safe) secondary side control. Gate driver outputs come with a high 5 A reverse current capability and 150 V/ns CMTI robustness for high dv/dt power loops. For slower switching or driving smaller MOSFETs, 1 A/2 A peak current product variants are available as well.

Device overview



Product family overview

Product key features

Fast power switching with accurate timing

- Available with 4 A/8 A and 1 A/2 A source/sink currents
- Propagation delay typ. 37 ns with 3 ns channel-to-channel precision
- › Max. propagation delay variation ~14 ns

Optimized for area and system BOM

- Isolation and driver in one package
- Low power dissipation due to low on-resistance
- Output stages with 5 A reverse current capability

Robustness against switching noise

- Floating drivers are able to handle large inductive voltage over- and undershoots
- Very good common mode transient immunity
 CMTI >150 V/ns
- Undervoltage lockout function for switch protection

Output- to -output channel isolation

> Functional level galvanic isolation

Input- to output channel isolation

> Functional and reinforced galvanic isolation

Product benefits

Efficiency gain and lower losses

- Lower switching losses in half-bridges due to fast and accurate turn on/off
- Perfect for new digital, fast high resolution PWM control including light load optimization

Improved thermal behavior at smaller form factor

- LGA with 1 mm, DSO with 2.3 mm package height versus volume > 1 cm for pulse transformers
- Eliminates two costly protection diodes on the gate driver outputs

Protection and safe operation

- Ideal for use in high power designs with fast switching transients
- Reliable CT coreless transformer PWM signal chain to turn on high side MOSFETs

Flexible configurations

HS+LS, HS+HS, LS+LS or 2x Imax on 1xHS

Regulatory safety

- > Functional for primary-side control
- Reinforced for secondary-side control

System benefits

Enabling higher system efficiency and higher power density designs

Improving long term competitive cost position, integration and mass manufacturability

Extending end-product lifetime

by improving safe operation of power switches in normal and abnormal field (grid) conditions

Lower EMI by ground isolation, driver proximity to MOSFETs or the use of 4-pin Kelvin source MOSFETs

Simplified safety approval through component (UL1577) and system (IEC60950, IEC62368) certificates













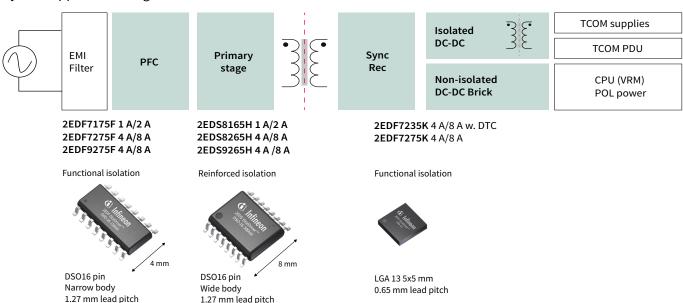




Dual-channel isolated EiceDRIVER™ family

Fast, robust, dual-channel, functional and reinforced isolated Si and SiC MOSFET gate driver ICs with accurate and stable timing

System application diagram



Product portfolio

Part number	Orderable part number (OPN)	Package	Input type	Driver source/ sink current	Gate driver UVLO	Input to output isolation				Dead-
						Isolation class	Rating	Surge testing	Safety certification	time control
2EDF7175F	2EDF7175FXUMA1	NB-DSO16 10 x 6 mm	Dual-mode (IN_A, IN_B)	1 A/2 A	4 V		$V_{IO} = 1.5 \text{ kV}_{DC}$	n.a.	n.a.	- no
2EDF7275F	2EDF7275FXUMA1			4 A/8 A	4 V	Functional				
2EDF9275F	2EDF9275FXUMA1				13 V					
2EDS8165H	2EDS8165HXUMA1	WB-DSO16 10.3 x 10.3 mm		1 A/2 A	0.1/	Reinforced	V _{IOTM} = 8 kV _{peak} V _{ISO} = 5.7 kV _{rms} (UL1577)	VIOCM - IO KV post	UL1577 IEC60950 IEC62368 CQC	
2EDS8265H	2EDS8265HXUMA1			4 A/8 A	8 V					
2EDS9265H	2EDS9265HXUMA1				13 V					
2EDF7235K	2EDF7235KXUMA1	LGA13 5.0 x 5.0 mm			4 V	Functional	$V_{IO} = 1.5 \text{ kV}_{DC}$	n.a.	n.a.	yes
2EDF7275K	2EDF7275KXUMA1									no

www.infineon.com/2EDi

Published by Infineon Technologies Austria AG 9500 Villach, Austria

© 2020 Infineon Technologies AG. All Rights Reserved.

THIS DOCUMENT IS FOR INFORMATION PURPOSES ONLY AND ANY INFORMATION GIVEN HEREIN SHALL IN NO EVENT BE REGARDED AS A WARRANTY, GUARANTEE OR DESCRIPTION OF ANY FUNCTIONALITY, CONDITIONS AND/OR QUALITY OF OUR PRODUCTS OR ANY SUITABILITY FOR A PARTICULAR PURPOSE. WITH REGARD TO THE TECHNICAL SPECIFICATIONS OF OUR PRODUCTS. WE KINDLY ASK YOU TO REFER TO THE RELEVANT PRODUCT DATA SHEETS PROVIDED BY US. OUR CUSTOMERS AND THEIR TECHNICAL DEPARTMENTS ARE REQUIRED TO EVALUATE THE SUITABILITY OF OUR PRODUCTS FOR THE INTENDED APPLICATION.

WE RESERVE THE RIGHT TO CHANGE THIS DOCUMENT AND/OR THE INFORMATION GIVEN HEREIN AT ANY TIME.

Additional information

For further information on technologies, our products, the application of our products, delivery terms and conditions and/or prices, please contact your nearest Infineon Technologies office (www.infineon.com).

Warnings

Due to technical requirements, our products may contain dangerous substances. For information on the types in question, please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by us in a written document signed by authorized representatives of Infineon Technologies, our products may not be used in any lifeendangering applications, including but not limited to medical, nuclear, military, life-critical or any other applications where a failure of the product or any consequences of the use thereof can result in personal injury

Order Number: B152-I1066-V1-7600-EU-EC-P

单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon(英飞凌)